

APPLICATION DATA SHEET

Electronic Version 0.0.11

Stylesheet Version: 1.0

Publication Filing Type: new-utility

Application Type: utility

Title of Invention: TRANSISTOR STRUCTURE WITH THICK RECESSED SOURCE/DRAIN
STRUCTURES AND FABRICATION PROCESS OF SAME

Legal Representative:

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INVENTOR(s):

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$\frac{d}{dt} \left(\frac{\partial L}{\partial \dot{x}} \right) = \frac{\partial L}{\partial x}$